

DUAL DAMASCENE PROCESS WITH NO PASSING METAL FEATURES

ABSTRACT OF THE DISCLOSURE

The present invention provides a method of forming integrated circuit interconnect structures wherein a passing metal feature 5 does not include a landing pad. In an exemplary embodiment, the method includes forming a via opening through first and second dielectric layers, such as silicon dioxide layer, located over a conductive layer, such as copper, and to a first etch stop layer, such as silicon nitride, located over the conductive layer. A trench opening is then formed through the second dielectric layer and to a second etch stop layer. Once the via and trench openings 10 are formed, an etch is conducted that etches through the first etch stop layer such that the opening contacts the underlying conductive layer.